

Peter J Wellmann

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145
papers

1,084
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19
h-index

26
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173
ext. papers

1,274
ext. citations

1.4
avg, IF

4.65
L-index

#	Paper	IF	Citations
145	Application of optical absorbance for the investigation of electronic and structural properties of sol-gel processed TiO ₂ films. <i>Thin Solid Films</i> , 2008 , 516, 7256-7259	2.2	86
144	Electrical, optical and morphological properties of nanoparticle indium tin oxide layers. <i>Thin Solid Films</i> , 2007 , 515, 8567-8572	2.2	52
143	Advances in wide bandgap SiC for optoelectronics. <i>European Physical Journal B</i> , 2014 , 87, 1	1.2	46
142	Ammonothermal Synthesis of Earth-Abundant Nitride Semiconductors ZnSiN and ZnGeN and Dissolution Monitoring by In Situ X-ray Imaging. <i>Chemistry - A European Journal</i> , 2017 , 23, 12275-12282	4.8	43
141	Review of SiC crystal growth technology. <i>Semiconductor Science and Technology</i> , 2018 , 33, 103001	1.8	36
140	Power Electronic Semiconductor Materials for Automotive and Energy Saving Applications - SiC, GaN, GaO, and Diamond. <i>Zeitschrift Fur Anorganische Und Allgemeine Chemie</i> , 2017 , 643, 1312-1322	1.3	36
139	SiC single crystal growth by a modified physical vapor transport technique. <i>Journal of Crystal Growth</i> , 2005 , 275, e555-e560	1.6	34
138	Cubic silicon carbide as a potential photovoltaic material. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 145, 104-108	6.4	32
137	Single Domain 3C-SiC Growth on Off-Oriented 4H-SiC Substrates. <i>Crystal Growth and Design</i> , 2015 , 15, 2940-2947	3.5	31
136	Conductance Enhancement Mechanisms of Printable Nanoparticulate Indium Tin Oxide (ITO) Layers for Application in Organic Electronic Devices. <i>Advanced Engineering Materials</i> , 2009 , 11, 295-301	3.5	27
135	Intermetallic compounds dynamic formation during annealing of stacked elemental layers and its influences on the crystallization of Cu ₂ ZnSnSe ₄ films. <i>Materials Chemistry and Physics</i> , 2013 , 142, 311-317	1.4	26
134	Growth of SiC bulk crystals for application in power electronic devices [process design, 2D and 3D X-ray in situ visualization and advanced doping. <i>Crystal Research and Technology</i> , 2015 , 50, 2-9	1.3	24
133	Nucleation Control of Cubic Silicon Carbide on 6H- Substrates. <i>Crystal Growth and Design</i> , 2012 , 12, 197-204	3.4	22
132	Conductivity and adhesion enhancement in low-temperature processed indium tin oxide/polymer nanocomposites. <i>Thin Solid Films</i> , 2010 , 518, 2910-2915	2.2	21
131	Bulk growth of SiC [review on advances of SiC vapor growth for improved doping and systematic study on dislocation evolution. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 1239-1256	1.3	21
130	In situ visualization of SiC physical vapor transport crystal growth. <i>Journal of Crystal Growth</i> , 2005 , 275, e1807-e1812	1.6	20
129	Determination of GaN solubility in supercritical ammonia with NH ₄ F and NH ₄ Cl mineralizer by in situ x-ray imaging of crystal dissolution. <i>Journal of Crystal Growth</i> , 2015 , 418, 64-69	1.6	19

128	Tuning the emission colour by manipulating terbium-terbium interactions: Terbium doped aluminum nitride as an example system. <i>Journal of Applied Physics</i> , 2013 , 114, 073518	2.5	19
127	Stability Criteria for 4H-SiC Bulk Growth. <i>Materials Science Forum</i> , 2001 , 353-356, 25-28	0.4	19
126	Numerical Simulation of Thermal Stress Formation During PVT-Growth of SiC Bulk Crystals. <i>Materials Science Forum</i> , 2001 , 353-356, 65-68	0.4	17
125	Low-temperature processing of transparent conductive indium tin oxide nanocomposites using polyvinyl derivatives. <i>Thin Solid Films</i> , 2011 , 520, 1341-1347	2.2	13
124	Broadband and omnidirectional light harvesting enhancement of fluorescent SiC. <i>Optics Express</i> , 2012 , 20, 7575-9	3.3	13
123	Investigation of a PVT SiC-Growth Set-up Modified by an Additional Gas Flow. <i>Materials Science Forum</i> , 2001 , 353-356, 33-36	0.4	13
122	Quantitative Study of the Role of Supersaturation during Sublimation Growth on the Yield of 50 mm 3C-SiC. <i>Materials Science Forum</i> , 2015 , 821-823, 77-80	0.4	12
121	Formation of Cu ₂ SnSe ₃ from stacked elemental layers investigated by combined in situ X-ray diffraction and differential scanning calorimetry techniques. <i>Journal of Alloys and Compounds</i> , 2014 , 588, 254-258	5.7	12
120	Ceramic liner technology for ammonoacidic synthesis. <i>Journal of Supercritical Fluids</i> , 2015 , 99, 76-87	4.2	12
119	Determination of dislocation density in MOVPE grown GaN layers using KOH defect etching. <i>Journal of Crystal Growth</i> , 2008 , 310, 955-958	1.6	11
118	Solubility and dissolution kinetics of GaN in supercritical ammonia in presence of ammonoacidic and ammonobasic mineralizers. <i>Journal of Crystal Growth</i> , 2017 , 479, 59-66	1.6	10
117	Optimization of growth parameters for growth of high quality heteroepitaxial 3CβSiC films at 1200°C. <i>Thin Solid Films</i> , 2015 , 577, 88-93	2.2	10
116	High Al-Doping of SiC Using a Modified PVT (M-PVT) Growth Set-Up. <i>Materials Science Forum</i> , 2005 , 483-485, 31-34	0.4	10
115	Epitaxial Metal Halide Perovskites by Inkjet-Printing on Various Substrates. <i>Advanced Functional Materials</i> , 2020 , 30, 2004612	15.6	10
114	Observation of Lattice Plane Bending during SiC PVT Bulk Growth Using In Situ High Energy X-Ray Diffraction. <i>Materials Science Forum</i> , 2010 , 645-648, 29-32	0.4	9
113	Fabrication, charge carrier transport, and application of printable nanocomposites based on indium tin oxide nanoparticles and conducting polymer 3,4-ethylenedioxythiophene/polystyrene sulfonic acid. <i>Journal of Applied Physics</i> , 2011 , 110, 104301	2.5	9
112	Study of Boron Incorporation During PVT Growth of p-type SiC Crystals. <i>Materials Science Forum</i> , 2001 , 353-356, 49-52	0.4	9
111	Polycrystalline SiC as Source Material for the Growth of Fluorescent SiC Layers. <i>Materials Science Forum</i> , 2013 , 740-742, 39-42	0.4	8

110	Analysis of Graphitization during Physical Vapor Transport Growth of Silicon Carbide. <i>Materials Science Forum</i> , 2004 , 457-460, 55-58	0.4	8
109	Modified Physical Vapor Transport Growth of SiC - Control of Gas Phase Composition for Improved Process Conditions. <i>Materials Science Forum</i> , 2005 , 483-485, 25-30	0.4	8
108	Chemical stability of carbon-based inorganic materials for in situ x-ray investigations of ammonothermal crystal growth of nitrides. <i>Journal of Crystal Growth</i> , 2016 , 456, 33-42	1.6	8
107	Growth of Large-Area, Stress-Free, and Bulk-Like 3C-SiC (100) Using 3C-SiC-on-Si in Vapor Phase Growth. <i>Materials</i> , 2019 , 12,	3.5	7
106	Analysis of the Basal Plane Dislocation Density and Thermomechanical Stress during 100 mm PVT Growth of 4H-SiC. <i>Materials</i> , 2019 , 12,	3.5	7
105	Cathodoluminescence characterization of organic semiconductor materials for light emitting device applications. <i>Journal of Applied Physics</i> , 2007 , 101, 113704	2.5	7
104	Influence of the growth interface shape on the defect characteristics in the facet region of 4H-SiC single crystals. <i>Journal of Crystal Growth</i> , 2020 , 532, 125436	1.6	7
103	In-situ phase formation study of copper indium diselenide absorber layers from CuIn nanoparticles and evaporated selenium. <i>Thin Solid Films</i> , 2013 , 535, 133-137	2.2	6
102	In Situ Observation of Polytype Switches during SiC PVT Bulk Growth by High Energy X-Ray Diffraction. <i>Materials Science Forum</i> , 2009 , 615-617, 23-26	0.4	6
101	Results of SIMS, LTPL and Temperature-Dependent Hall Effect Measurements Performed on Al-Doped SiC Substrates Grown by the M-PVT Method. <i>Materials Science Forum</i> , 2006 , 527-529, 633-636 ^{0.4}	0.4	6
100	In Situ X-Ray Measurements of Defect Generation during PVT Growth of SiC. <i>Materials Science Forum</i> , 2007 , 556-557, 267-270	0.4	6
99	Investigation of Mass Transport during SiC PVT Growth Using Digital X-Ray Imaging, ¹³ C Labeling of Source Material and Numerical Modeling. <i>Materials Science Forum</i> , 2003 , 433-436, 9-12	0.4	6
98	Growth Rate Control in SiC-Physical Vapor Transport Method Through Heat Transfer Modeling and Non-Stationary Process Conditions. <i>Materials Science Forum</i> , 2000 , 338-342, 39-42	0.4	6
97	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. <i>Materials</i> , 2021 , 14,	3.5	6
96	Depth-resolved and temperature dependent analysis of phase formation processes in Cu ₂ ZnSnSe films on ZnO substrates. <i>Journal of Materials Science: Materials in Electronics</i> , 2017 , 28, 7730-7738	2.1	5
95	Limitations during Vapor Phase Growth of Bulk (100) 3C-SiC Using 3C-SiC-on-SiC Seeding Stacks. <i>Materials</i> , 2019 , 12,	3.5	5
94	Synthesis of In ₂ Se ₃ and Cu _{2-x} Se Micro- and Nanoparticles with Microwave-Assisted Solvothermal and Aqueous Redox Reactions for the Preparation and Stabilization of Printable Precursors for a CuInSe ₂ Solar Cell Absorber Layer. <i>Energy Procedia</i> , 2015 , 84, 62-70	2.3	5
93	Low temperature processing of hybrid nanoparticulate Indium Tin Oxide (ITO) polymer layers and application in large scale lighting devices. <i>Thin Solid Films</i> , 2011 , 519, 5744-5747	2.2	5

92	Determination of Exciton Capture Cross-Sections of Neutral Nitrogen Donor on Cubic and Hexagonal Sites in n-Type (N) 6H-SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 341-344	0.4	5
91	Impact of Compensation on Optical Absorption Bands in the Below-Bandgap Region in n-Type (N) 6H-SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 333-336	0.4	5
90	Development of a KOH Defect Etching Furnace with Absolute In-Situ Temperature Measurement Capability. <i>Materials Science Forum</i> , 2005 , 483-485, 283-286	0.4	5
89	Absorption Measurements and Doping Level Evaluation in n-Type and p-Type 4H-SiC and 6H-SiC. <i>Materials Science Forum</i> , 2001 , 353-356, 397-400	0.4	5
88	Flow Stability, Convective Heat Transfer and Chemical Reactions in Ammonothermal Autoclaves Insights by In Situ Measurements of Fluid Temperatures. <i>Crystals</i> , 2020 , 10, 723	2.3	5
87	Influence of Morphological Changes in a Source Material on the Growth Interface of 4h-SiC Single Crystals. <i>Materials</i> , 2019 , 12,	3.5	4
86	Prospects of Bulk Growth of 3C-SiC Using Sublimation Growth. <i>Materials Science Forum</i> , 2020 , 1004, 113-119	1.1	4
85	Towards X-ray in-situ visualization of ammonothermal crystal growth of nitrides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 1439-1442		4
84	Modeling of the Mass Transport during Homo-Epitaxial Growth of Silicon Carbide by Fast Sublimation Epitaxy. <i>Materials Science Forum</i> , 2013 , 740-742, 52-55	0.4	4
83	Basal Plane Dislocation Dynamics in Highly p-Type Doped versus Highly n-Type Doped SiC. <i>Materials Science Forum</i> , 2006 , 527-529, 79-82	0.4	4
82	Growth and Characterization of ¹³ C Enriched 4H-SiC for Fundamental Materials Studies. <i>Materials Science Forum</i> , 2007 , 556-557, 13-16	0.4	4
81	Growth of Phosphorous-Doped n-Type 6H-SiC Crystals using a Modified PVT Technique and Phosphine as Source. <i>Materials Science Forum</i> , 2004 , 457-460, 727-730	0.4	4
80	Photoluminescence Study of In-Situ Rare Earth Doped PVT-Grown SiC Single Crystals. <i>Materials Science Forum</i> , 2005 , 483-485, 445-448	0.4	4
79	SiC Crystal Growth from the Vapor and Liquid Phase. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 640, 1		4
78	Digital X-Ray Imaging of SiC PVT Process: Analysis of Crystal Growth and Powder Source Degradation. <i>Materials Science Forum</i> , 2000 , 338-342, 71-74	0.4	4
77	Intentional Incorporation and Tailoring of Point Defects during Sublimation Growth of Cubic Silicon Carbide by Variation of Process Parameters. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900286 ¹⁻³		4
76	Modeling of the PVT Growth Process of Bulk 3C-SiC - Growth Process Development and Challenge of the Right Materials Data Base. <i>Materials Science Forum</i> , 2019 , 963, 157-160	0.4	3
75	Numerical reactive diffusion modeling of stacked elemental layer rapid thermal annealed chalcopyrite absorber layer formation. <i>Thin Solid Films</i> , 2015 , 582, 397-400	2.2	3

74	Step-Flow Growth of Fluorescent 4H-SiC Layers on 4 Degree Off-Axis Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 185-188	0.4	3
73	Towards the Growth of SiGeC Epitaxial Layers for the Application in Si Solar Cells. <i>Energy Procedia</i> , 2015 , 84, 236-241	2.3	3
72	Real-time Investigations on the Formation of CuIn(S,Se) ₂ while annealing precursors with varying sulfur content. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1165, 1		3
71	Determination of material inhomogeneities in . <i>Energy Procedia</i> , 2010 , 2, 183-188	2.3	3
70	Progress and Limits of the Numerical Simulation of SiC Bulk and Epitaxy Growth Processes. <i>Materials Science Forum</i> , 2005 , 483-485, 3-8	0.4	3
69	Electronic Raman Studies of Shallow Donors in Silicon Carbide. <i>Materials Science Forum</i> , 2006 , 527-529, 579-584	0.4	3
68	Micro-Optical Characterization Study of Highly p-Type Doped SiC:Al Wafers. <i>Materials Science Forum</i> , 2005 , 483-485, 393-396	0.4	3
67	Impact of SiC Source Material on Temperature Field and Vapor Transport During SiC PVT Crystal Growth Process. <i>Materials Science Forum</i> , 2001 , 353-356, 11-14	0.4	3
66	Aluminum Doping of 6H- and 4H-SiC with a Modified PVT Growth Method. <i>Materials Science Forum</i> , 2002 , 389-393, 131-134	0.4	3
65	On the Excitation Mechanism of Erbium and Ytterbium in the Quaternary Compounds InGaAsP. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 422, 255		3
64	On the importance of dislocation flow in continuum plasticity models for semiconductor materials. <i>Journal of Crystal Growth</i> , 2020 , 532, 125414	1.6	3
63	Overgrowth of Protrusion Defects during Sublimation Growth of Cubic Silicon Carbide Using Free-Standing Cubic Silicon Carbide Substrates. <i>Crystal Growth and Design</i> , 2021 , 21, 4046-4054	3.5	3
62	An adhesive bonding approach by hydrogen silsesquioxane for silicon carbide-based LED applications. <i>Materials Science in Semiconductor Processing</i> , 2019 , 91, 9-12	4.3	3
61	Impact of Varying Parameters on the Temperature Gradients in 100mm Silicon Carbide Bulk Growth in a Computer Simulation Validated by Experimental Results. <i>Crystal Research and Technology</i> , 2020 , 55, 1900121	1.3	3
60	Annealing-Induced Changes in the Nature of Point Defects in Sublimation-Grown Cubic Silicon Carbide. <i>Materials</i> , 2019 , 12,	3.5	2
59	Optimising The Parameters For The Synthesis Of CuIn-Nanoparticles By Chemical Reduction Method For Chalcopyrite Thin Film Precursors. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1538, 203-208		2
58	Germanium Incorporation during PVT Bulk Growth of Silicon Carbide. <i>Materials Science Forum</i> , 2009 , 615-617, 11-14	0.4	2
57	Generation of Void-Like Structures during Hot-Hydrogen Etching of Si Substrates for 3C-SiC Epitaxy. <i>Materials Science Forum</i> , 2011 , 679-680, 127-130	0.4	2

56	Modeling and Experimental Verification of SiC M-PVT Bulk Crystal Growth. <i>Materials Science Forum</i> , 2006 , 527-529, 75-78	0.4	2
55	Contactless Electrical Defect Characterization and Topography of a-Plane Grown Epitaxial Layers. <i>Materials Science Forum</i> , 2007 , 556-557, 327-330	0.4	2
54	Impact of n-Type versus p-Type Doping on Mechanical Properties and Dislocation Evolution during SiC Crystal Growth. <i>Materials Science Forum</i> , 2007 , 556-557, 259-262	0.4	2
53	On the Origin of the Below Band-Gap Absorption Bands in n-Type (N) 4H- and 6H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 645-648	0.4	2
52	Electrical and Optical Characterization of p-Type Boron-Doped 6H-SiC Bulk Crystals. <i>Materials Science Forum</i> , 2003 , 433-436, 337-340	0.4	2
51	In situ Synthesis of Source Material from Elemental Si and C during SiC PVT Growth Process and Characterization Using Digital X-Ray Imaging. <i>Materials Science Forum</i> , 2002 , 389-393, 91-94	0.4	2
50	Characterization of protrusions and stacking faults in 3C-SiC grown by sublimation epitaxy using 3C-SiC-on-Si seeding layers. <i>Advanced Materials Proceedings</i> , 2017 , 2, 774-778	1	2
49	The search for new materials and the role of novel processing routes. <i>Discover Materials</i> , 2021 , 1, 14		2
48	Deep Electronic Levels in n-Type and p-Type 3C-SiC. <i>Materials Science Forum</i> , 2019 , 963, 297-300	0.4	2
47	Vapor Growth of 3C-SiC Using the Transition Layer of 3C-SiC on Si CVD Templates. <i>Materials Science Forum</i> , 2019 , 963, 149-152	0.4	2
46	Bulk Growth of SiC [Review on Advances of SiC Vapor Growth for Improved Doping and Systematic Study on Dislocation Evolution] 1-31		2
45	Large Area Growth of Cubic Silicon Carbide Using Close Space PVT by Application of Homoepitaxial Seeding. <i>Materials Science Forum</i> , 1062 , 74-78	0.4	2
44	3C-SiC Bulk Sublimation Growth on CVD Hetero-Epitaxial Seeding Layers. <i>Materials Science Forum</i> , 2017 , 897, 15-18	0.4	1
43	Vacuum-Free and Highly Dense Nanoparticle Based Low-Band-Gap CuInSe ₂ Thin-Films Manufactured by Face-to-Face Annealing with Application of Uniaxial Mechanical Pressure. <i>Coatings</i> , 2019 , 9, 484	2.9	1
42	Low temperature formation of CuIn _{1-x} Ga _x Se ₂ solar cell absorbers by all printed multiple species nanoparticulate Se + CuIn + CuGa precursors. <i>Thin Solid Films</i> , 2015 , 582, 60-68	2.2	1
41	Characterization of kesterite thin films fabricated by rapid thermal processing of stacked elemental layers using spatially resolved cathodoluminescence. <i>Thin Solid Films</i> , 2015 , 582, 387-391	2.2	1
40	Solution Growth of Silicon Carbide Using the Vertical Bridgman Method. <i>Crystal Research and Technology</i> , 2018 , 53, 1800019	1.3	1
39	Morphological and Optical Stability in Growth of Fluorescent SiC on Low Off-Axis Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 19-22	0.4	1

38	Application of 3-D X-Ray Computed Tomography for the In Situ Visualization of the SiC Crystal Growth Interface during PVT Bulk Growth. <i>Materials Science Forum</i> , 2013 , 740-742, 27-30	0.4	1
37	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Transactions</i> , 2017 , 80, 107-115		1
36	Real-Time Measurement of the Evolution of Growth Facets during SiC PVT Bulk Growth Using 3-D X-Ray Computed Tomography. <i>Materials Science Forum</i> , 2014 , 778-780, 9-12	0.4	1
35	Lateral Boron Distribution in Polycrystalline SiC Source Materials. <i>Materials Science Forum</i> , 2013 , 740-742, 397-400	0.4	1
34	Fundamental Study of the Temperature Ramp-Up Influence for 3C-SiC Hetero-Epitaxy on Silicon (100). <i>Materials Science Forum</i> , 2010 , 645-648, 151-154	0.4	1
33	P- and n-Type Doping in SiC Sublimation Epitaxy Using Highly Doped Substrates. <i>Materials Science Forum</i> , 2009 , 615-617, 85-88	0.4	1
32	Efficient Image Segmentation for Detection of Dislocations in High Resolution Light Microscope Images of SiC Wafers. <i>Materials Science Forum</i> , 2011 , 679-680, 277-281	0.4	1
31	Freestanding 3C-SiC Grown by Sublimation Epitaxy Using 3C-SiC Templates on Silicon. <i>Materials Science Forum</i> , 2012 , 717-720, 177-180	0.4	1
30	Defect Etching of Non-Polar and Semi-Polar Faces in SiC. <i>Materials Science Forum</i> , 2007 , 556-557, 243-246.	0.4	1
29	In-Situ Er-Doping of SiC Bulk Single Crystals. <i>Materials Science Forum</i> , 2004 , 457-460, 723-726	0.4	1
28	Acceptor-Hydrogen Interaction in Ternary III-V Semiconductors. <i>Materials Science Forum</i> , 1995 , 196-201, 987-992	0.4	1
27	Dislocation Formation During Physical Vapor Transport Growth of 4 H-SiC Crystals 2021 , 1-32		1
26	Investigation of the Growth Kinetics of SiC Crystals during Physical Vapor Transport Growth by the Application of In Situ 3D Computed Tomography Visualization. <i>Advanced Engineering Materials</i> , 2020 , 22, 1900778	3.5	1
25	Optimization of the SiC Powder Source Size Distribution for the Sublimation Growth of Long Crystals Boules. <i>Materials Science Forum</i> , 2019 , 963, 42-45	0.4	1
24	Tracking of the Growth Interface during PVT-Growth of SiC Boules Using a X-Ray Computed Tomography Setup. <i>Materials Science Forum</i> , 2019 , 963, 14-17	0.4	1
23	Advances in In Situ SiC Growth Analysis Using Cone Beam Computed Tomography. <i>Materials Science Forum</i> , 2019 , 963, 5-9	0.4	1
22	Comparison of Achievable Contrast Features in Computed Tomography Observing the Growth of a 4H-SiC Bulk Crystal. <i>Materials</i> , 2019 , 12,	3.5	1
21	Determination of site occupancy of boron in 6H-SiC by multiple-wavelength neutron holography. <i>Applied Physics Letters</i> , 2022 , 120, 132101	3.4	1

20	Chemical Vapor Deposition of 3C-SiC on [100] Oriented Silicon at Low Temperature < 1200°C for Photonic Applications. <i>Materials Science Forum</i> , 1062, 119-124	0.4	1
19	Photoluminescence-Topography of the p-Type Doped SiC Wafers for Determination of Doping Inhomogeneity. <i>Materials Science Forum</i> , 2009, 615-617, 259-262	0.4	0
18	Bulk Growth of SiC. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1069, 1		0
17	Influence of Growth Temperature on the Evolution of Dislocations during PVT Growth of Bulk SiC Single Crystals. <i>Materials Science Forum</i> , 2007, 556-557, 263-266	0.4	0
16	Influence of the growth conditions on the formation of macro-steps on the growth interface of SiC-Crystals. <i>Journal of Crystal Growth</i> , 2021, 576, 126361	1.6	0
15	Growth Conditions and In Situ Computed Tomography Analysis of Facetted Bulk Growth of SiC Boules. <i>Materials Science Forum</i> , 2018, 924, 245-248	0.4	
14	Photoluminescence Topography of Fluorescent SiC and its Corresponding Source Crystals. <i>Materials Science Forum</i> , 2013, 740-742, 421-424	0.4	
13	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P741-P745		2
12	Progress on Numerical Reactive Diffusion Modeling of CuInSe ₂ Phase Formation for Solar Cell Applications. <i>Energy Procedia</i> , 2015, 84, 86-92		2.3
11	Microsecond Carrier Lifetimes in Bulk-Like 3C-SiC Grown by Sublimation Epitaxy. <i>Materials Science Forum</i> , 2013, 740-742, 315-318	0.4	
10	Fabrication of Broadband Antireflective Sub-Wavelength Structures on Fluorescent SiC. <i>Materials Science Forum</i> , 2013, 740-742, 1024-1027	0.4	
9	Defect Structures at the Silicon/3C-SiC Interface. <i>Materials Science Forum</i> , 2012, 717-720, 423-426	0.4	
8	Silicon Carbide Growth: C/Si Ratio Evaluation and Modeling. <i>Materials Research Society Symposia Proceedings</i> , 2006, 911, 2		
7	Structural Defects in SiC Crystals Investigated by High Energy X-Ray Diffraction. <i>Materials Science Forum</i> , 2004, 457-460, 339-342	0.4	
6	Status of 3 C - SiC Growth and Device Technology 2021, 93-136		
5	Novel Theoretical Approaches for Understanding and Predicting Dislocation Evolution and Propagation 2021, 199-223		
4	In Situ Visualization of the Ammonothermal Crystallization Process by X-ray Technology. <i>Springer Series in Materials Science</i> , 2021, 171-190	0.9	
3	Special Equipment for Ammonothermal Processes. <i>Springer Series in Materials Science</i> , 2021, 317-328	0.9	

- 2 Applicability of a Flat-Bed Birefringence Setup for the Determination of Threading Dislocations of Silicon Carbide Wafers. *Materials Science Forum*,1062, 113-118 0.4
- 1 <i>In Situ</i> Monitoring of Unintentionally Released Nitrogen Gas in the Initial PVT Silicon Carbide Growth Process Using Mass Spectrometry. *Materials Science Forum*,1062, 79-83 0.4